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March 2008 Special Issue on Non-volatile Memories beyond Tera-bit

Journal of Semiconductor Technology and Science will publish a special issue on “Tera-bit Level Non-volatile Memories”. It will provide an overview of recent progress in the development of tera-bit-level non-volatile memory for improving device operation speed, retention-time, and endurance characteristic.

Topics

- Nano floating-gate random-access-memory(NFGM)
- Polymer random-access-memory(PoRAM)
- Resistive random-access-memory(ReRAM)
- Phase change random-access-memory(PRAM)
- Tunnel Barrier Memory(TBM)
- Ferroelectric FET Memory(FFM)

Authors wishing to have their contributions considered for publication in this Special Issue, which will be published in March 2008 issue, are invited to submit an electronic copy of their manuscripts to Editor Prof. Jea-Gun Park (parkjgL@hanyang.ac.kr), at no later than January 31, 2008. Manuscripts should be submitted in free style double spaced MS word format as an e-mail attachment. See <http://www.jsts.org> for details. Both regular papers as well as letters are welcomed.

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